PNP General Purpose Transistor

The NST856BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 220-475
- Low $V_{CE(sat)}$, $\leq -0.3 \text{ V}$
- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-65	Vdc
Collector - Base Voltage	V _{CBO}	-80	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

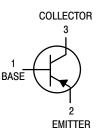
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm² 1 oz, copper traces.
- 2. 500 mm² 1 oz, copper traces.



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NST856BF3T5G



SOT-1123 CASE 524AA STYLE 1

MARKING DIAGRAM



A = Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST856BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I _C = -10 mA)	V _{(BR)CEO}	-65	-	-	V
Collector - Emitter Breakdown Voltage (I _C = -10 μA, V _{EB} = 0)	V _{(BR)CES}	-80	-	-	V
Collector – Base Breakdown Voltage (I _C = -10 μA)	V _{(BR)CBO}	-80	-	-	٧
Emitter – Base Breakdown Voltage (I _E = -1.0 μA)	V _{(BR)EBO}	-5.0	-	-	٧
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	I _{CBO}	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS		•	•	•	•
DC Current Gain $ \begin{array}{l} (I_C = -10 \; \mu \text{A, V}_{CE} = -5.0 \; \text{V}) \\ (I_C = -2.0 \; \text{mA, V}_{CE} = -5.0 \; \text{V}) \end{array} $	h _{FE}	- 220	150 290	- 475	_
Collector – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{CE(sat)}	- -	- -	-0.3 -0.8	V
Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage (I_C = -2.0 mA, V_{CE} = -5.0 V) (I_C = -10 mA, V_{CE} = -5.0 V)	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = -10 mA, V _{CE} = -5.0 Vdc, f = 100 MHz)	f⊤	100	-	_	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{obo}	_	_	4.5	pF
Input Capacitance (V _{EB} = -0.5 V, I _C = 0 mA, f = 1.0 MHz)	C _{ibo}	-	_	10	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	_	10	dB

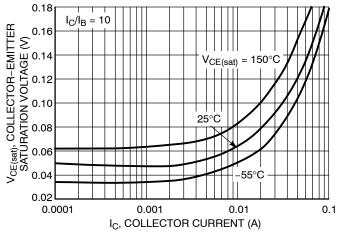


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

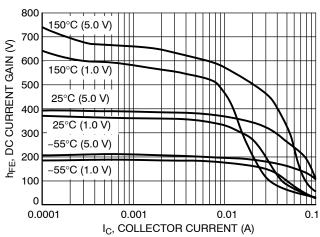


Figure 2. DC Current Gain vs. Collector Current

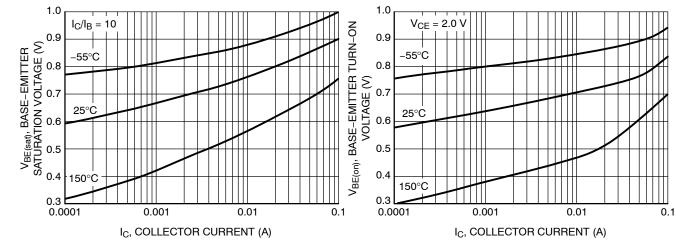


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 4. Base Emitter Turn-On Voltage vs. **Collector Current**

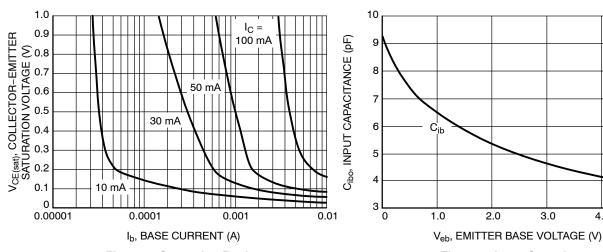


Figure 5. Saturation Region

Figure 6. Input Capacitance

4.0

5.0

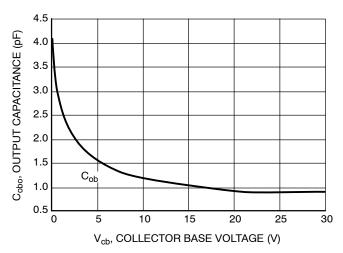
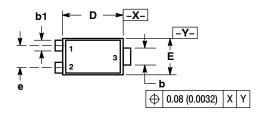
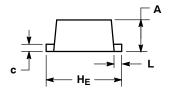


Figure 7. Output Capacitance

PACKAGE DIMENSIONS

SOT-1123 CASE 524AA-01 **ISSUE A**





- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS.
- 2. GONTHOLLING DIVINGSION. WILLING TELES.

 S MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

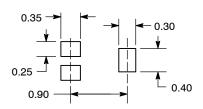
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	MON	MAX	
Α	0.34	0.37	0.40	0.013	0.015	0.016	
b	0.15	0.20	0.25	0.006	0.008	0.010	
b1	0.10	0.15	0.20	0.004	0.006	0.008	
С	0.07	0.12	0.17	0.003	0.005	0.007	
D	0.75	0.80	0.85	0.030	0.031	0.033	
E	0.55	0.60	0.65	0.022 0.024		0.026	
е	e 0.35			0.014			
HE	0.95	1.00	1.05	0.037	0.039	0.041	
L	0.05	0.10	0.15	0.002	0.004	0.006	

STYLE 1:

PIN 1. BASE 2. EMITTER

3. COLLECTOR

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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